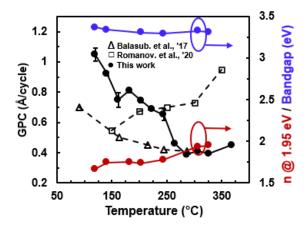
<u>Supplementary FIGURES: Mullapudi et al. Plasma Enhanced Atomic Layer of WO_x Using a Wide Temperature</u> <u>Stability Precursor</u>



15 $f_{dep} = 200^{\circ}C, 150 \text{ cycles}$ xx/15/60/30s $WSN-4/N_2/O_2 \text{ plasma/N}_2$ 0 2 4 6 WSN-4 pulse (s)

Fig. 1. GPC (black circles), refractive index (red circles) at 1.95 eV, and bandgap (blue circles) vs. temperature for 300 cycle ALD WO_x film on silicon. Open symbols show GPC values from other

Fig. 2. Thickness vs. WSN-4 pulse time for a 150 cycle WO_x film deposited at 200°C.

precursors in literature.

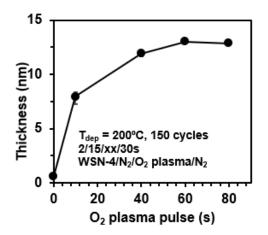


Fig 3. Thickness vs. O_2 plasma pulse time for a 150 cycles WO_x film deposited at 200°C.

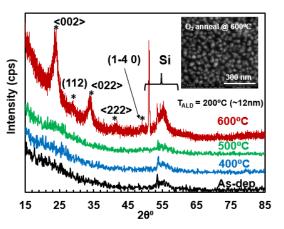


Fig 4. GI-XRD of a 200°C, 150 cycle film isochronally (60 minutes) annealed in O_2 at up to 600°C. Triclinic WO₃ phase seen at 600°C (REF: JCPDS 20-1323). Inset shows a plan SEM image of a 600°C annealed film.